

N-channel 650 V, 1.2 Ω typ., 4 A MDmesh™ M2 Power MOSFETs in TO-220FP, TO-220 and IPAK packages

Datasheet - preliminary data

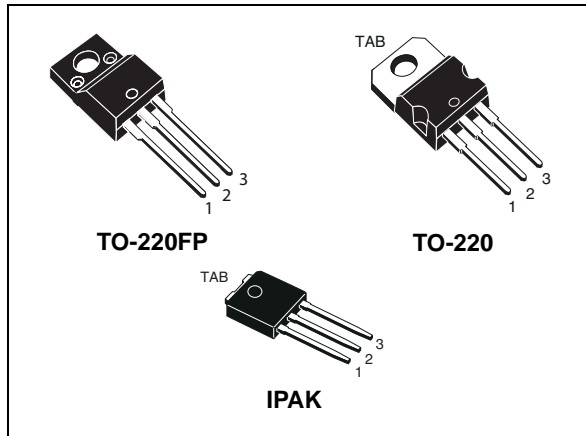
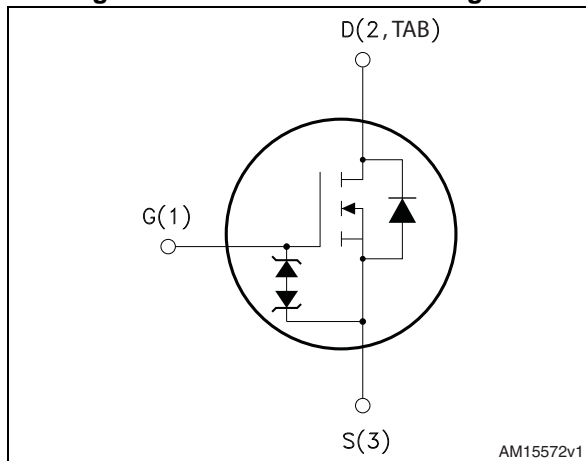


Figure 1. Internal schematic diagram



Features

Order codes	V_{DS}	$R_{DS(on) \max}$	I_D
STF6N65M2	650 V	1.35 Ω	4 A
STP6N65M2			
STU6N65M2			

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, the devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STF6N65M2	6N65M2	TO-220FP	Tube
STP6N65M2		TO-220	
STU6N65M2		IPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220FP	TO-220, IPAK	
V_{GS}	Gate-source voltage	± 25		V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	4 ⁽¹⁾	4	A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	2.5 ⁽¹⁾	2.5	A
$I_{DM}^{(2)}$	Drain current (pulsed)	16 ⁽¹⁾	16	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	20	60	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{ s}$; $T_C=25\text{ °C}$)	2500		V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15		V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50		
T_{stg}	Storage temperature	- 55 to 150		°C
T_j	Max. operating junction temperature			

- Limited by maximum junction temperature.
- Pulse width limited by safe operating area.
- $I_{SD} \leq 4\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD}=400\text{ V}$
- $V_{DS} \leq 520\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		TO-220FP	TO-220	IPAK	
$R_{thj-case}$	Thermal resistance junction-case max	6.25	2.08		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5		100	°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	0.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25\text{ °C}$, $I_D = I_{AR}$; $V_{DD}=50$)	100	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0, V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 2\text{ A}$		1.2	1.35	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	226	-	pF
C_{oss}	Output capacitance		-	12.8	-	pF
C_{rss}	Reverse transfer capacitance		-	0.65	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	114	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	6.5	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 4\text{ A}, V_{GS} = 10\text{ V}$ (see Figure 8)	-	9.8	-	nC
Q_{gs}	Gate-source charge		-	1.7	-	nC
Q_{gd}	Gate-drain charge		-	4	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

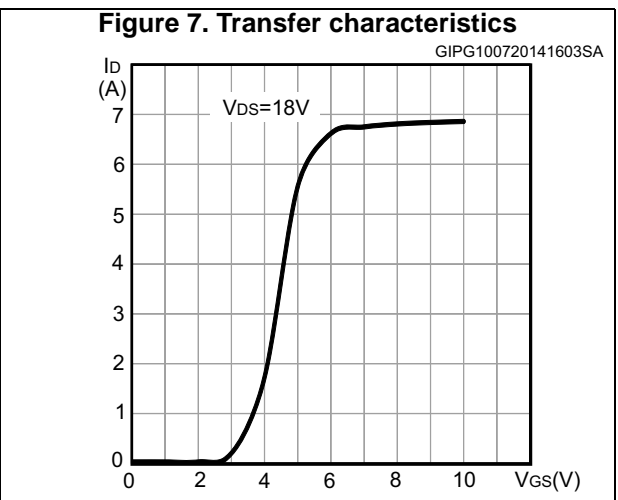
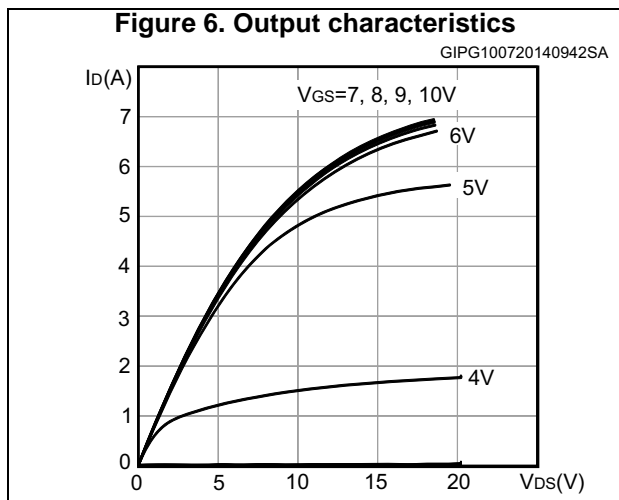
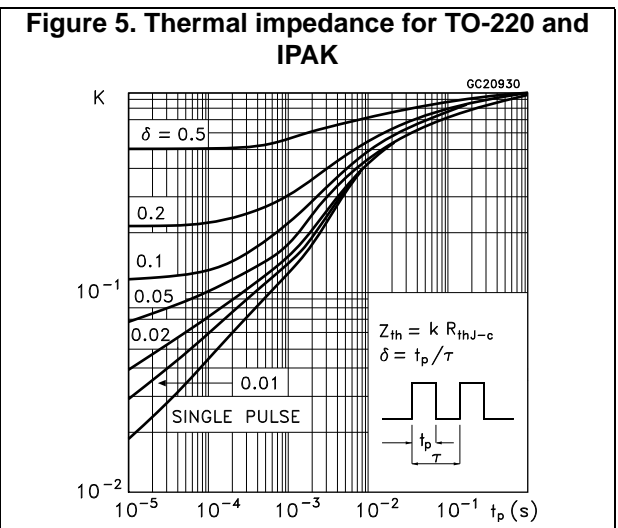
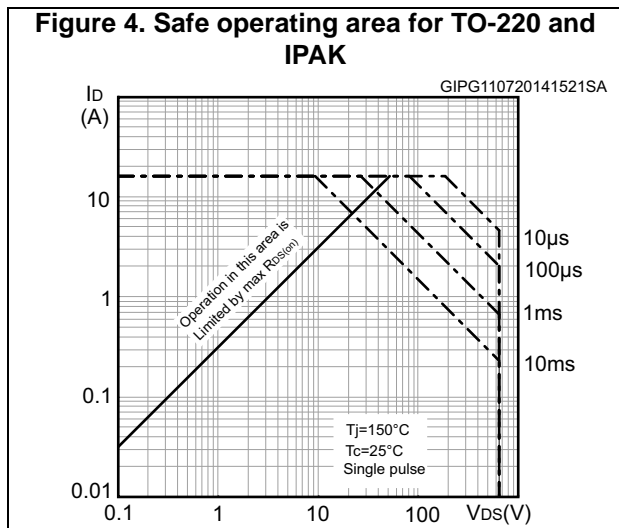
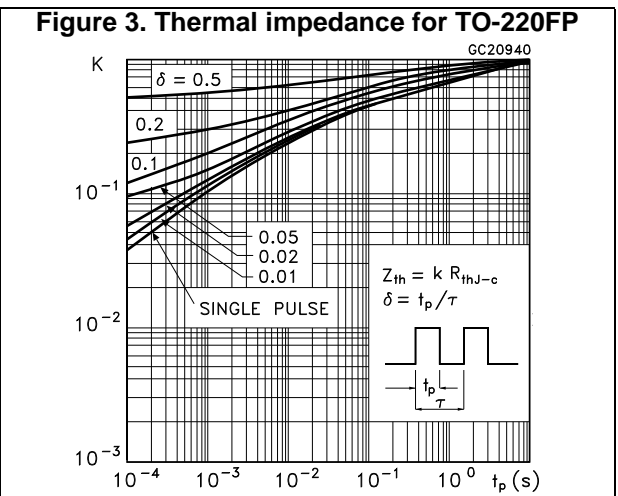
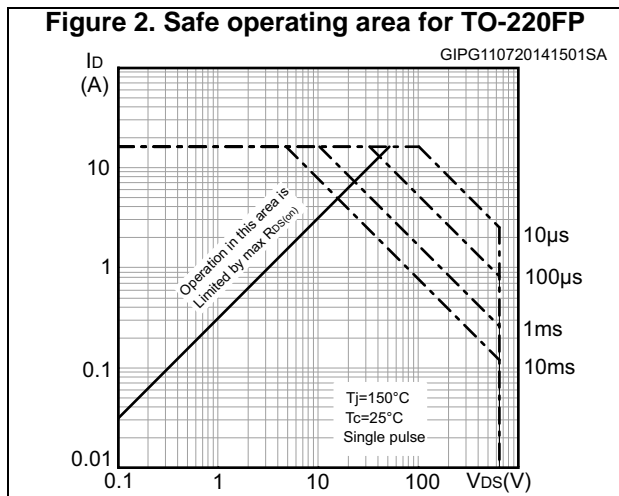
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}, I_D = 2\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 15 and Figure 20)	-	19	-	ns
t_r	Rise time		-	7	-	ns
$t_{d(off)}$	Turn-off delay time		-	6.5	-	ns
t_f	Fall time		-	20	-	ns

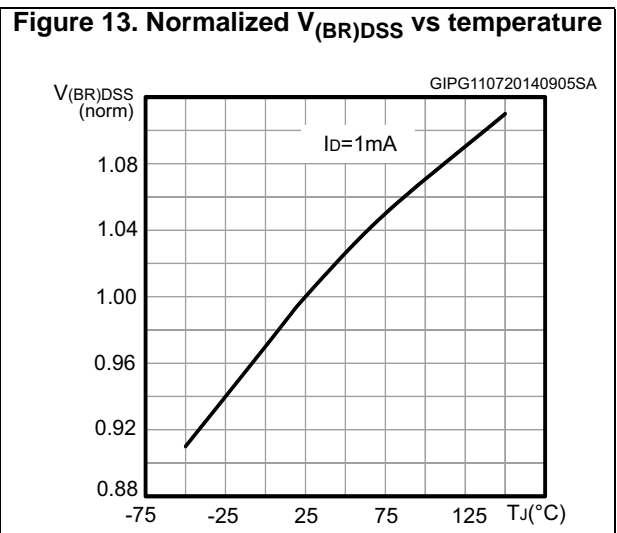
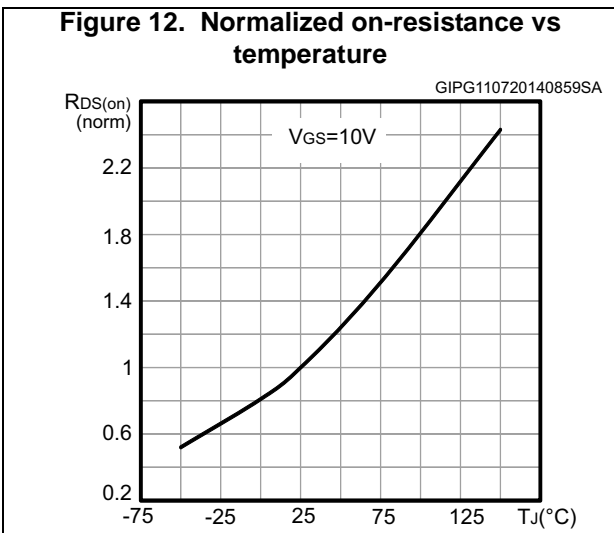
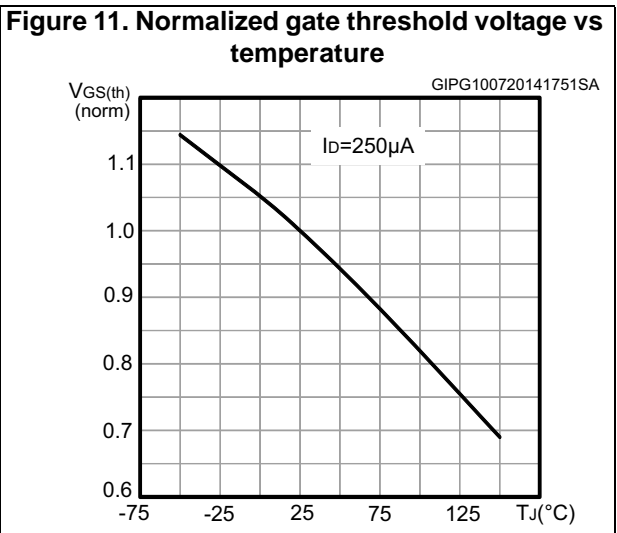
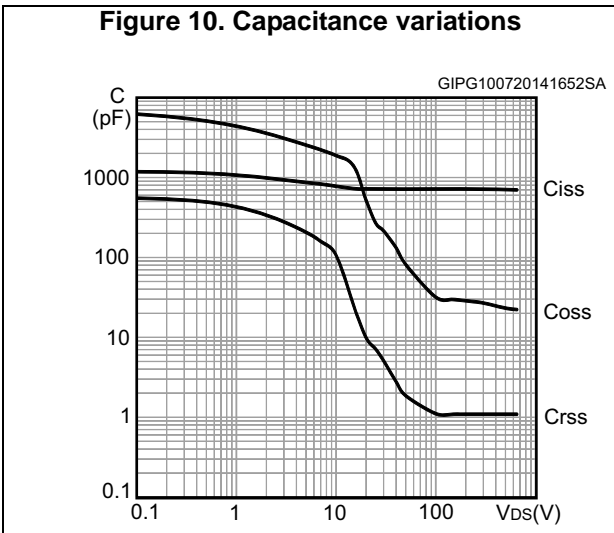
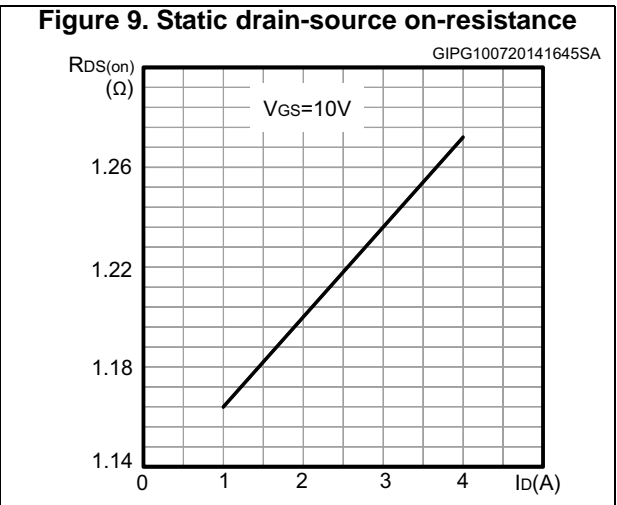
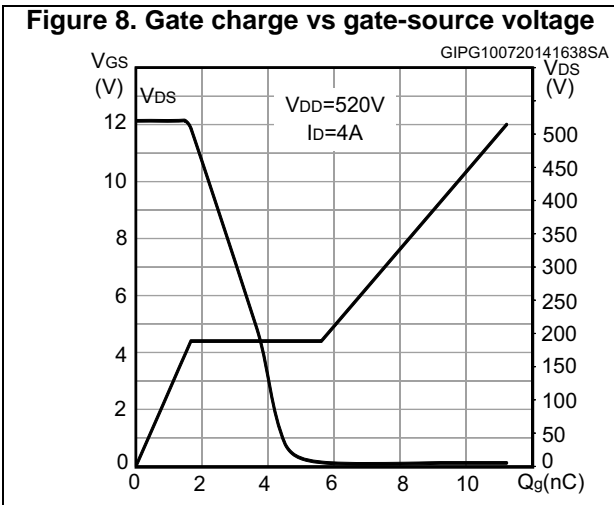
Table 8. Source drain diode

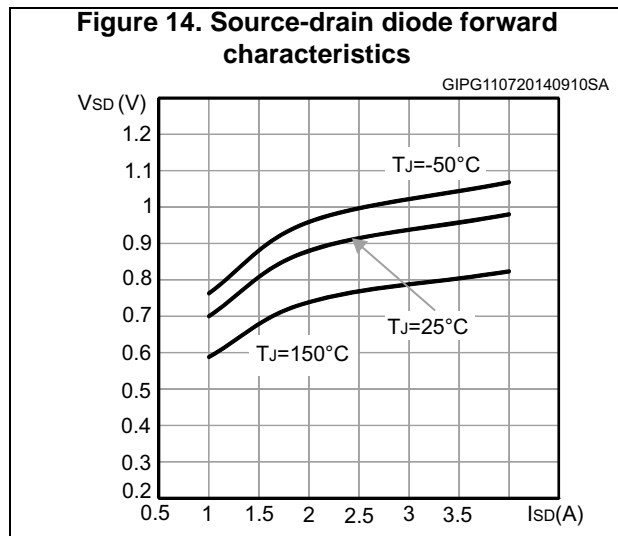
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		4	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		16	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 4 \text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 4 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see Figure 17)	-	260		ns
Q_{rr}	Reverse recovery charge		-	1.2		μC
I_{RRM}	Reverse recovery current		-	9.2		A
t_{rr}	Reverse recovery time	$I_{SD} = 4 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$ (see Figure 17)	-	400		ns
Q_{rr}	Reverse recovery charge		-	1.84		μC
I_{RRM}	Reverse recovery current		-	9.1		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

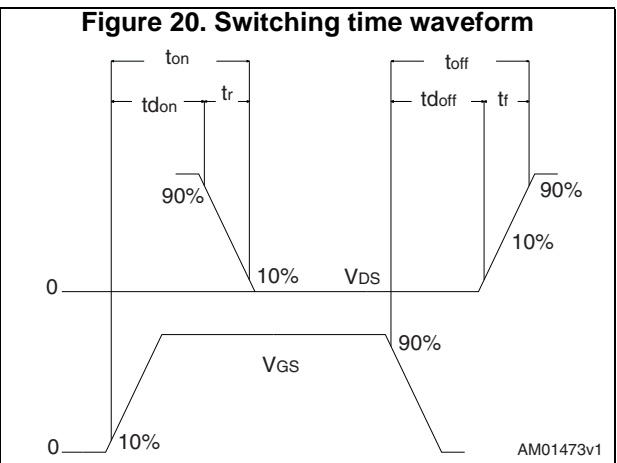
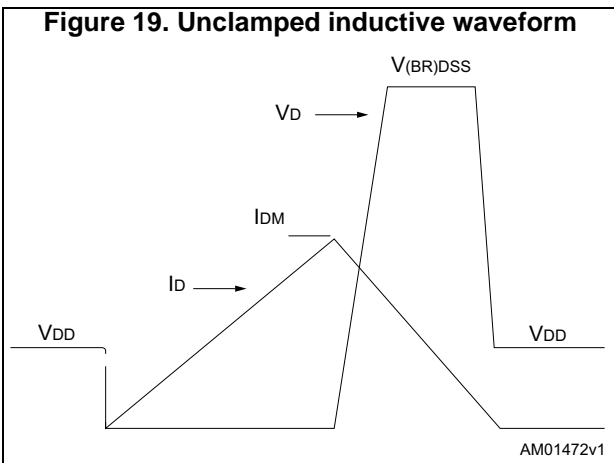
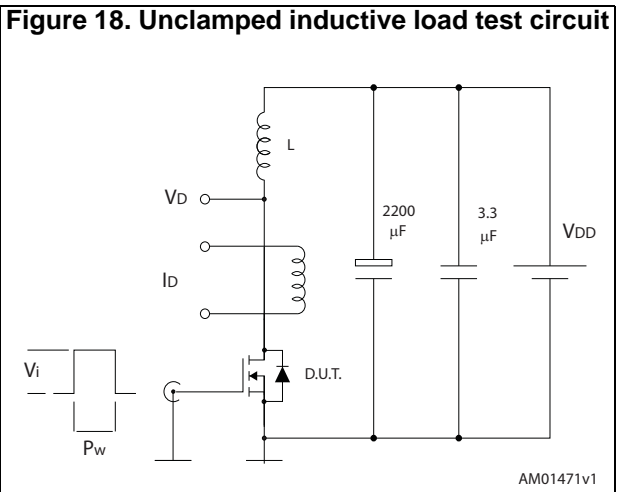
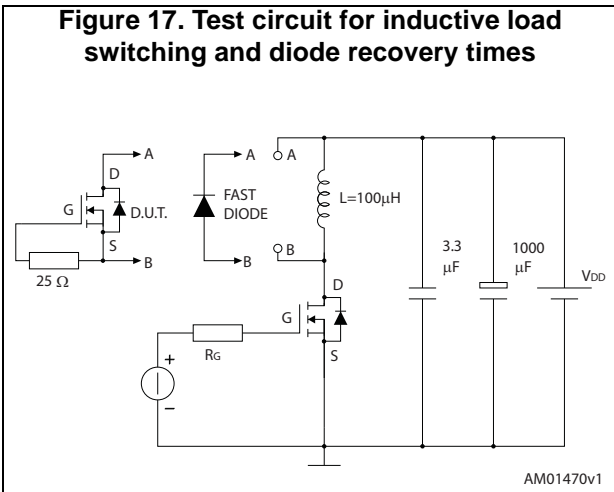
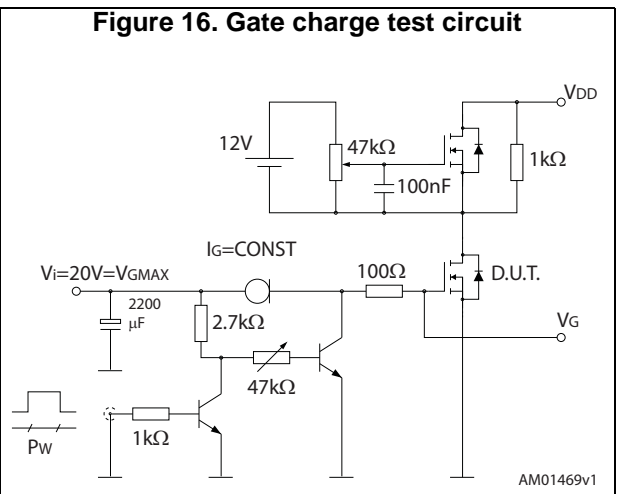
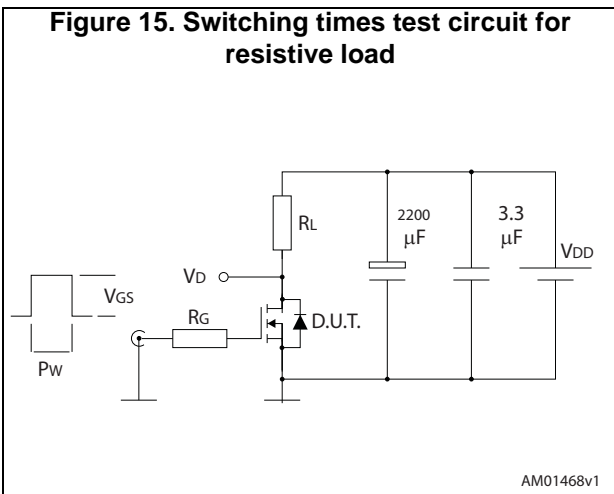
2.1 Electrical characteristics (curves)







3 Test circuits

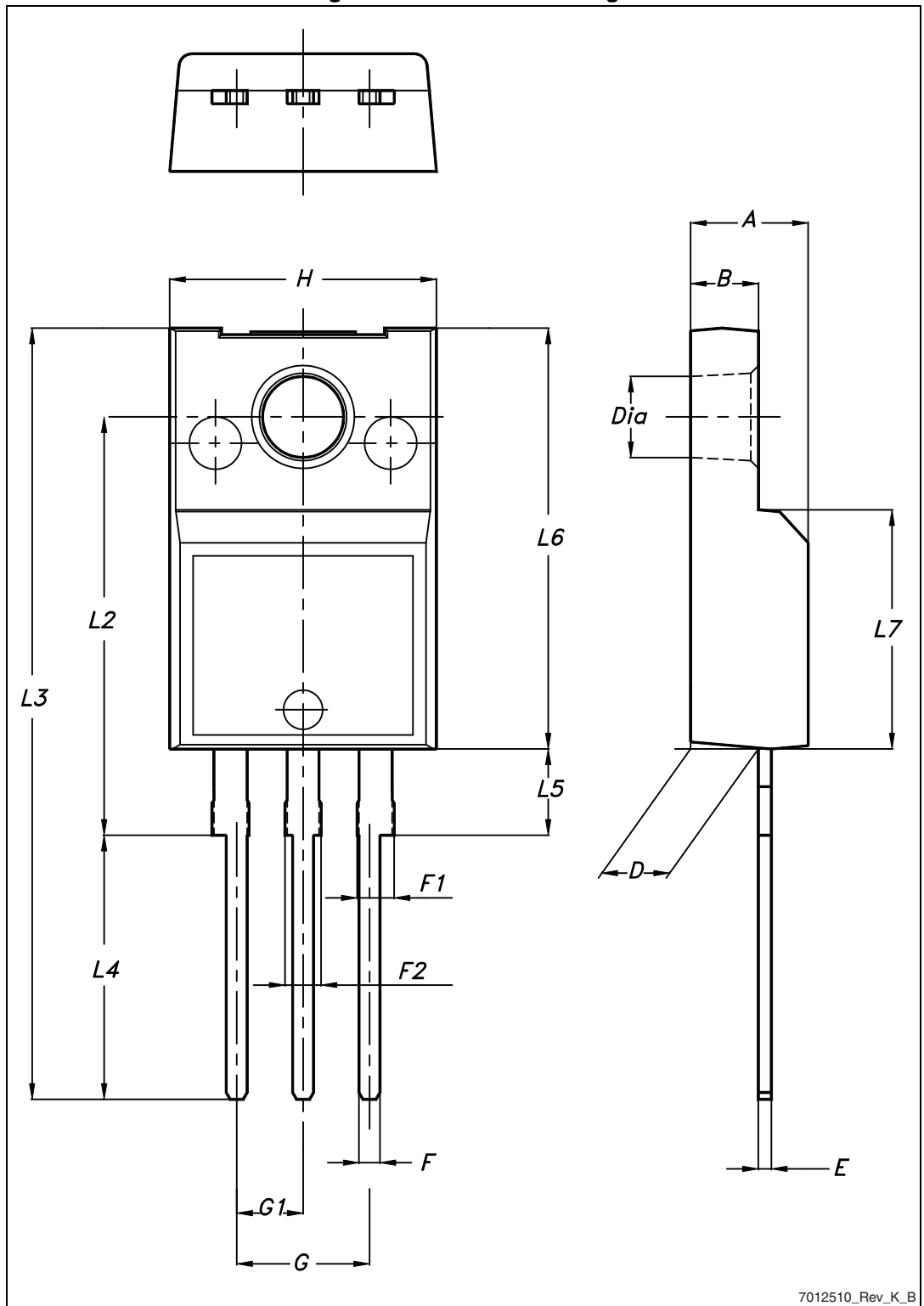


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

4.1 TO-220FP, STF6N65M2

Figure 21. TO-220FP drawing



7012510_Rev_K_B

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Ø	3		3.2

4.2 TO-220, STP6N65M2

Figure 22. TO-220 type A drawing

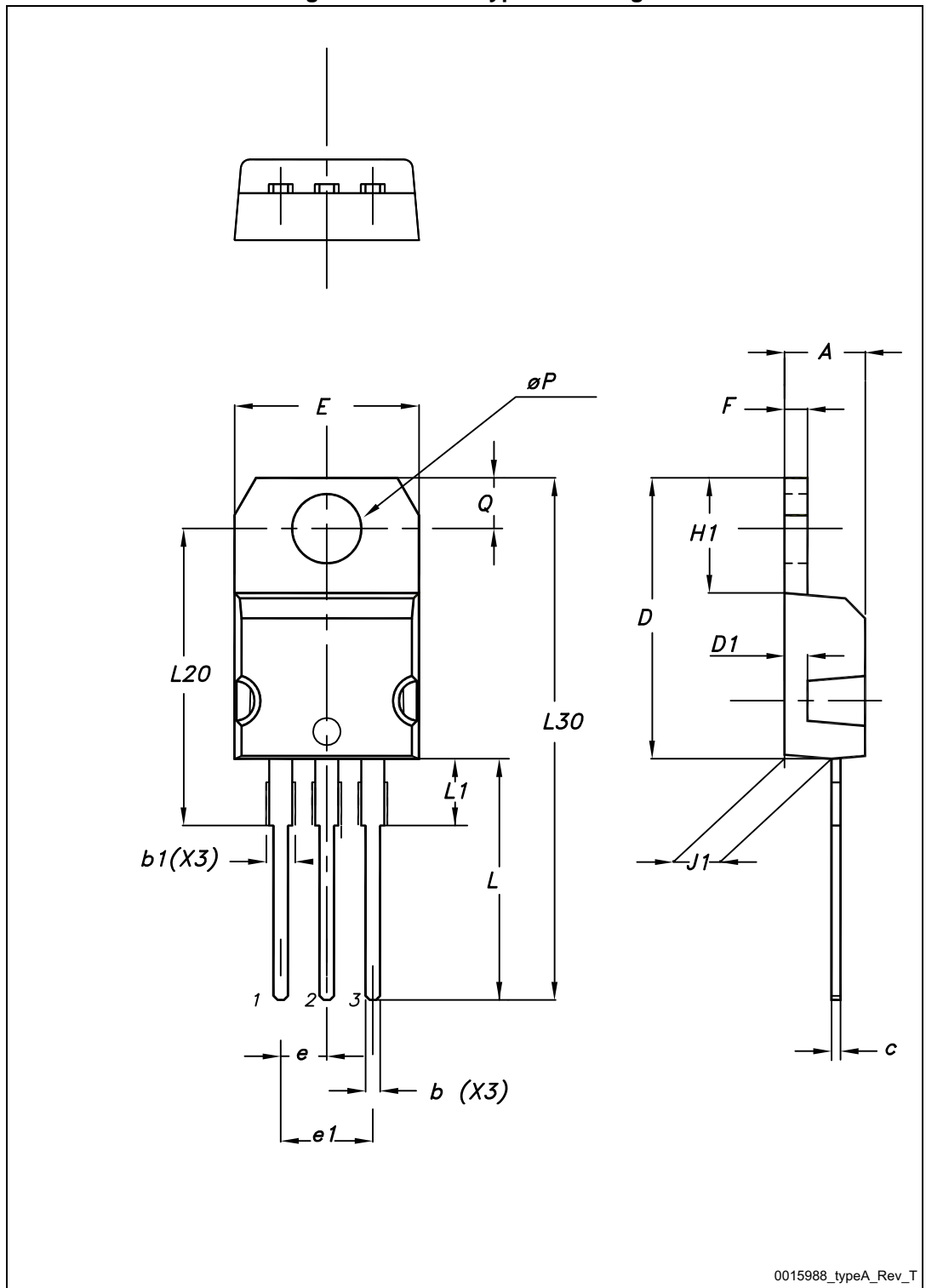
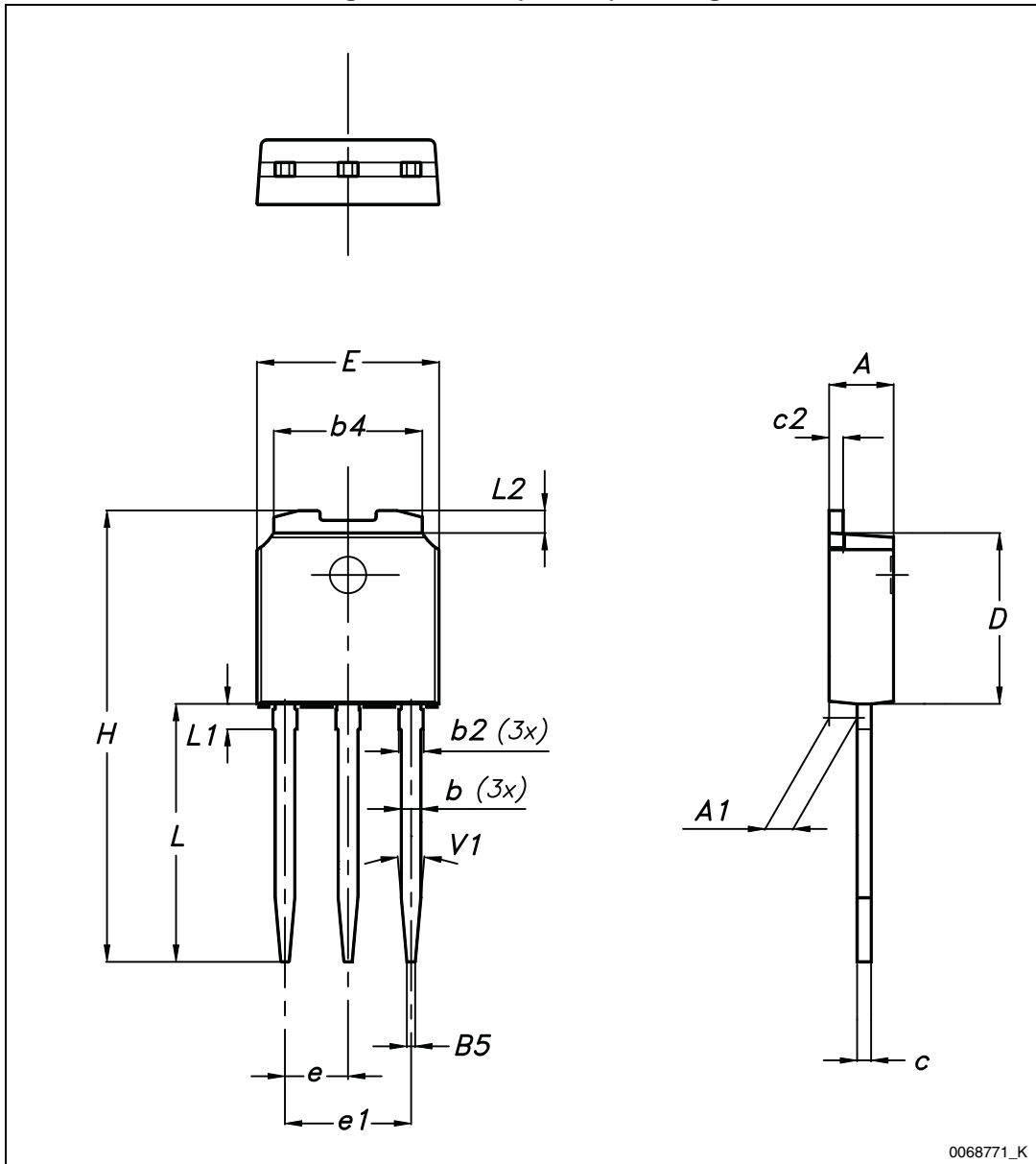


Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

4.3 IPAK, STU6N65M2

Figure 23. IPAK (TO-251) drawing



0068771_K

Table 11. IPAK (TO-251) mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

5 Revision history

Table 12. Document revision history

Date	Revision	Changes
04-Aug-2014	1	First release.

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